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内容概要

本书介绍了涉及集成电路组件的集成和设计的较宽范围的内容，提供给读者用简单公式估计晶体管几何尺寸和推演电路行为的方法。
这本独特的书广泛覆盖场效应管的设计、MOS管的建模和数字CMOS集成电路设基础以及MOS存储器结构和设计。
本书突出了在片上系统设计和集成方面知识增加的需求，第一次在单本中覆盖半导体物理学、数字VLSI设计和模拟集成电路，介绍了集成电路半导体组件的基本行为和基于MOS与BiCMOS工艺的数字和模拟集成电路的设计。

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